



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

DMBTA92

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

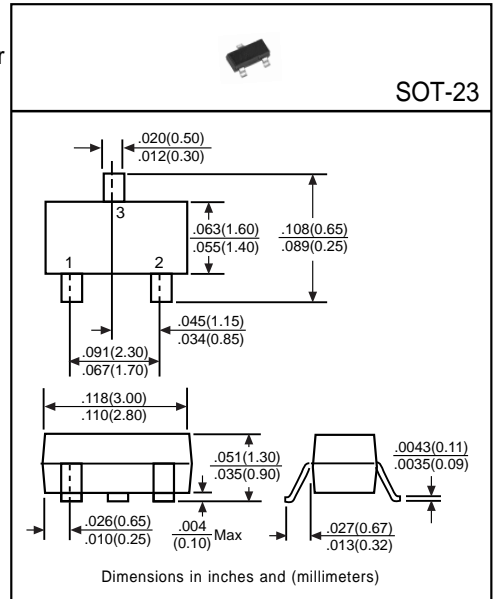
Designed for application as a video output to drive color CRT, or as a dialer circuit in electronics telephone.

Pinning

- 1 = Base
- 2 = Emitter
- 3 = Collector

Absolute Maximum Ratings (T<sub>A</sub>=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-300	V
Collector-Emitter Voltage	V <sub>CE0</sub>	-300	V
Emitter-Base Voltage	V <sub>EB0</sub>	-5	V
Collector Current	I <sub>C</sub>	-500	mA
Total Power Dissipation	P <sub>D</sub>	225	mW
Junction Temperature	T <sub>J</sub>	+150	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C



Electrical Characteristics

(Ratings at 25°C ambient temperature unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	-300	-	-	V	I <sub>C</sub> =-100μA
Collector-Emitter Breakdown Voltage	BV <sub>CE0</sub>	-300	-	-	V	I <sub>C</sub> =-1mA
Emitter-Base Breakdown Voltage	BV <sub>EB0</sub>	-5	-	-	V	I <sub>E</sub> =-10μA
Collector Cutoff Current	I <sub>CBO</sub>	-	-	-250	nA	V <sub>CB</sub> =-200V
Emitter Cutoff Current	I <sub>EBO</sub>	-	-	-100	nA	V <sub>EB</sub> =-3V
Collector-Emitter Saturation Voltage <sup>(1)</sup>	V <sub>CE(sat)</sub>	-	-	-0.5	V	I <sub>C</sub> =-20mA, I <sub>B</sub> =-2mA
Base-Emitter Saturation Voltage <sup>(1)</sup>	V <sub>BE(sat)</sub>	-	-	-0.9	V	I <sub>C</sub> =-20mA, I <sub>B</sub> =-2mA
DC Current Gain <sup>(1)</sup>	hFE1	25	-	-	-	I <sub>C</sub> =-1mA, V <sub>CE</sub> =-10V
	hFE2	40	-	-	-	I <sub>C</sub> =-10mA, V <sub>CE</sub> =-10V
	hFE3	25	-	-	-	I <sub>C</sub> =-30mA, V <sub>CE</sub> =-10V
Transition Frequency	f <sub>T</sub>	50	-	-	MHz	I <sub>C</sub> =-10mA, V <sub>CE</sub> =-20V, f=100MHz
Output Capacitance	C <sub>ob</sub>	-	-	6	pF	V <sub>CB</sub> =-20V, f=1MHz

(1) Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%